

APPLICATION INFORMATION

2 GHz low noise amplifier with the BFG480W

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ABSTRACT

- Description of the product
The BFG480W, one of the Philips double polysilicon wideband transistors of the BFG400W series.
- Application area
Low voltage high frequency wireless applications.
- Presented application
A low noise amplifier for 2 GHz.
- Main results
At a frequency of 2 GHz, the amplifier has an insertion power gain of approximately 9.5 dB, a noise figure of approximately 2.2 dB, and a third order intercept point of approximately 10 dBm (measured at input).

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INTRODUCTION

With the Philips double polysilicon wideband transistor BFG480W, it is possible to design Low Noise Amplifiers (LNAs) for high frequency applications with a low current and a low supply voltage. These amplifiers are well suited for the new generation low voltage high frequency wireless applications. One feature of the BFG480W is that it has a good linearity performance. Therefore the BFG480W is well suited for LNAs with high linearity demands, such as Code Division Multiple Access (CDMA) applications. This application note gives an example of a 2 GHz LNA with the BFG480W.

CIRCUIT DESCRIPTION

The following initial conditions apply for the amplifier design:

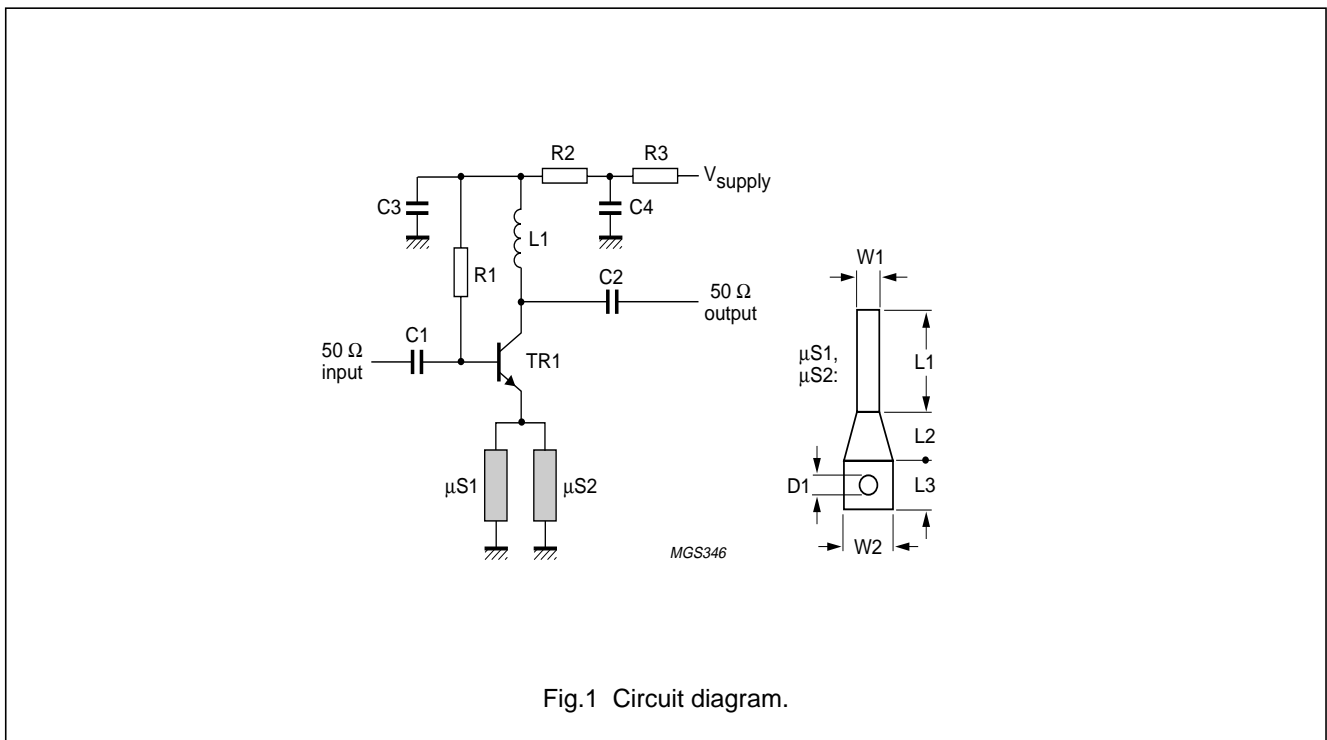
- $V_{\text{supply}} \approx 3.6 \text{ V}$
- $V_{\text{CE}} = 2 \text{ V}$
- $I_{\text{C}} = 21 \text{ mA}$
- $f = 2 \text{ GHz}$.

The circuit is designed to show the following performance:

- $|S_{21}|^2 \approx 9 \text{ dB}$
- $\text{NF} \leq 2.5 \text{ dB}$
- $\text{VSWR}_{\text{IN}} < 2$
- $\text{VSWR}_{\text{OUT}} < 2$
- $\text{IP3}_i > 9 \text{ dBm}$.

The output matching is realised with an LC combination. Also an extra emitter inductance (micro stripline) is used on both emitter-leads to improve the matching and the noise figure.

CIRCUIT DIAGRAM



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COMPONENT LIST

Table 1 Component list for the 2 GHz LNA

COMPONENT	VALUE	UNIT	SIZE, MANUFACTURER	PURPOSE, COMMENT
TR1	BFG480W		SOT343R	RF amplifier
R1	5.6	k Ω	0603; Philips	collector to base bias
R2	22	Ω	0603; Philips	RF blocking
R3	47	Ω	0603; Philips	collector series bias; levelling h_{FE} spread
R4	0	Ω	0603; Philips	(or a short circuit wire)
R5	0	Ω	0603; Philips	(or a short circuit wire)
C1	4.7	pF	0603; Philips	input match (base coupling)
C2	150	pF	0603; Philips	output match (collector coupling)
C3	5.6	pF	0603; Philips	2 GHz short (L1 to ground)
C4	1	nF	0603; Philips	RF collector bias decoupling
L1	18	nH	0805CS; Coilcraft	output match
μ S1	see Table 2			emitter induction: micro stripline and via-hole
μ S2	see Table 2			emitter induction; micro stripline and via-hole
PCB	FR4			$\epsilon_r \approx 4.6$; d = 0.5 mm

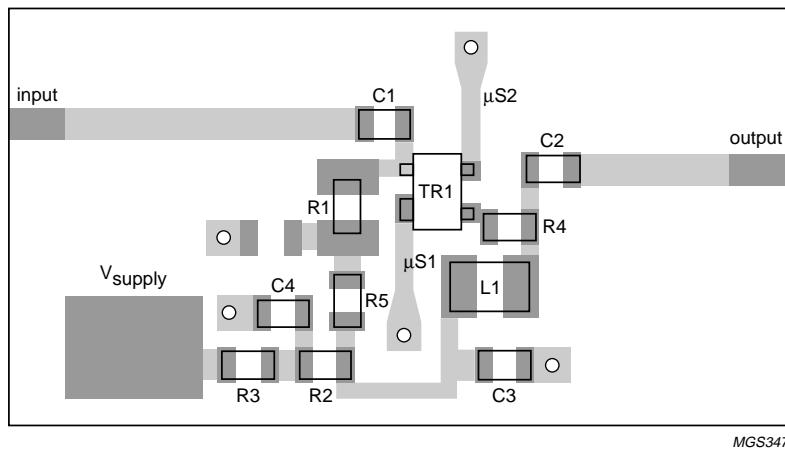
Table 2 Dimensions of the micro striplines μ S1 and μ S2 (see Fig.1)

DIMENSION	VALUE	UNIT	DESCRIPTION
L1	2.5	mm	length micro stripline; $Z_0 \approx 48 \Omega$
L2	1.0	mm	length interconnect micro stripline and via-hole area
L3	1.0	mm	length via-hole
W1	0.5	mm	width micro stripline
W2	1.0	mm	width via-hole area
D1	0.4	mm	diameter of via-hole

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BOARD LAYOUT

The layout has been designed with the Hewlett Packard Microwave Design System (HP-MDS).



MGS347

Fig.2 PCB layout.

MEASUREMENTS

The measurements have been done under the following conditions (unless otherwise specified):

- Supply voltage 3.6 V
- Supply current 21 mA
- Frequency 2 GHz.

Table 3 Measuring results of the 2 GHz LNA

SYMBOL	PARAMETER	CONDITION	VALUE	UNITS
$ S_{21} ^2$	insertion power gain		9.7	dB
$VSWR_{IN}$	input voltage standing wave ratio		1.9	
$VSWR_{OUT}$	output voltage standing wave ratio		1.2	
NF	noise figure		2.2	dB
$IP3_i$	third order intercept point	$\Delta f = 200$ kHz	10	dBm

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NOTES

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NOTES

Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 3 Figtree Drive, HOMEBUSH, NSW 2140,
Tel. +61 2 9704 8141, Fax. +61 2 9704 8139

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,
Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

Belgium: see The Netherlands

Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 68 9211, Fax. +359 2 68 9102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Sydhavnsgade 23, 1780 COPENHAGEN V,
Tel. +45 33 29 3333, Fax. +45 33 29 3905

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615 800, Fax. +358 9 6158 0920

France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex,
Tel. +33 1 4099 6161, Fax. +33 1 4099 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 2353 60, Fax. +49 40 2353 6300

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor,
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,
Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: PT Philips Development Corporation, Semiconductors Division,
Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,
Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Via Casati, 23 - 20052 MONZA (MI),
Tel. +39 039 203 6838, Fax +39 039 203 6800

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,
TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5057

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Pakistan: see Singapore

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Al.Jerozolimskie 195 B, 02-222 WARSAW,
Tel. +48 22 5710 000, Fax. +48 22 5710 001

Portugal: see Spain

Romania: see Italy

Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 319762,
Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria

Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 58088 Newville 2114,
Tel. +27 11 471 5401, Fax. +27 11 471 5398

South America: Al. Vicente Pinzon, 173, 6th floor,
04547-130 SÃO PAULO, SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 821 2382

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 93 301 6312, Fax. +34 93 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
Tel. +46 8 5985 2000, Fax. +46 8 5985 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,
Tel. +41 1 488 2741 Fax. +41 1 488 3263

Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,
TAIPEI, Taiwan Tel. +886 2 2134 2886, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,
Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Yukari Dudullu, Org. San. Blg., 2.Cad. Nr. 28 81260 Umraniye,
ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 208 730 5000, Fax. +44 208 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,
Tel. +381 11 62 5344, Fax.+381 11 63 5777

For all other countries apply to: Philips Semiconductors,
International Marketing & Sales Communications, Building BE-p, P.O. Box 218,
5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

Internet: <http://www.semiconductors.philips.com>

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